BTA2008 series D and E

0.8 A Three-quadrant triacs high commutation

Rev. 01 — 18 January 2008 Product data sheet

1. Product profile

1.1 General description

Passivated, guaranteed commutation, sensitive gate triacs in a SOT54 plastic package

1.2 Features

- Guaranteed commutation performance at each gate sensitivity
- Sensitive gate
- Easily interfaced with low power drivers including microcontrollers

1.3 Applications

- Motor control
- Solenoid drivers

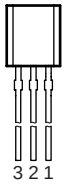
1.4 Quick reference data

- $V_{DRM} \leq 600$ V (BTA2008-600D)
- $V_{DRM} \leq 600$ V (BTA2008-600E)
- $V_{DRM} \leq 800$ V (BTA2008-800D)
- $V_{DRM} \leq 800$ V (BTA2008-800E)
- $I_{TSM} \leq 9$ A (t = 20 ms)
- $I_{GT} \leq 5$ mA (BTA2008-600D)
- $I_{GT} \leq 5$ mA (BTA2008-800D)
- $I_{GT} \leq 10$ mA (BTA2008-600E)
- $I_{GT} \leq 10$ mA (BTA2008-800E)
- $I_{T(RMS)} \leq 0.8$ A

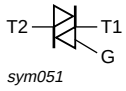
2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 2 (T2)		
2	gate (G)		
3	main terminal 1 (T1)		



SOT54 (TO-92)



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BTA2008-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BTA2008-600E			
BTA2008-800D			
BTA2008-800E			

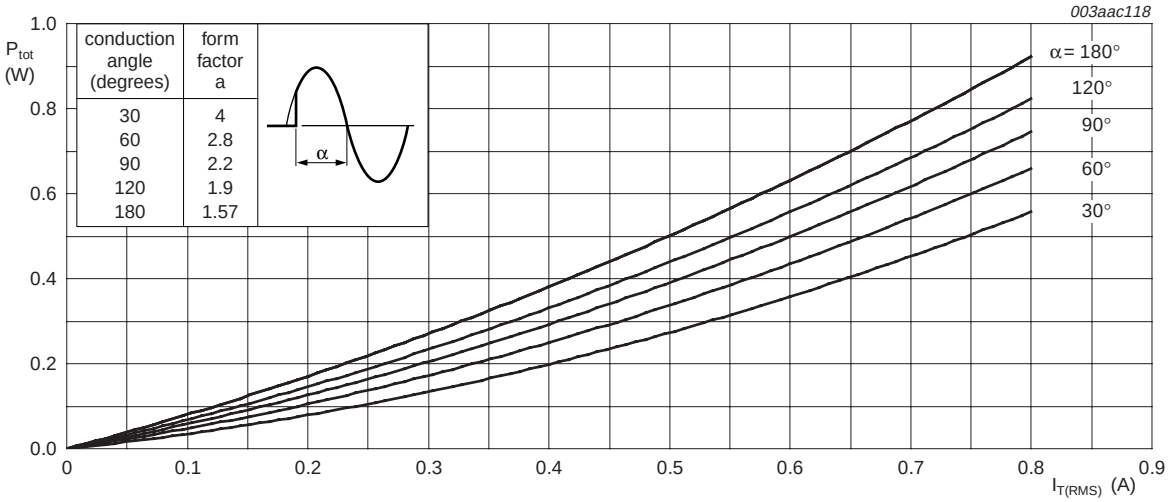
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

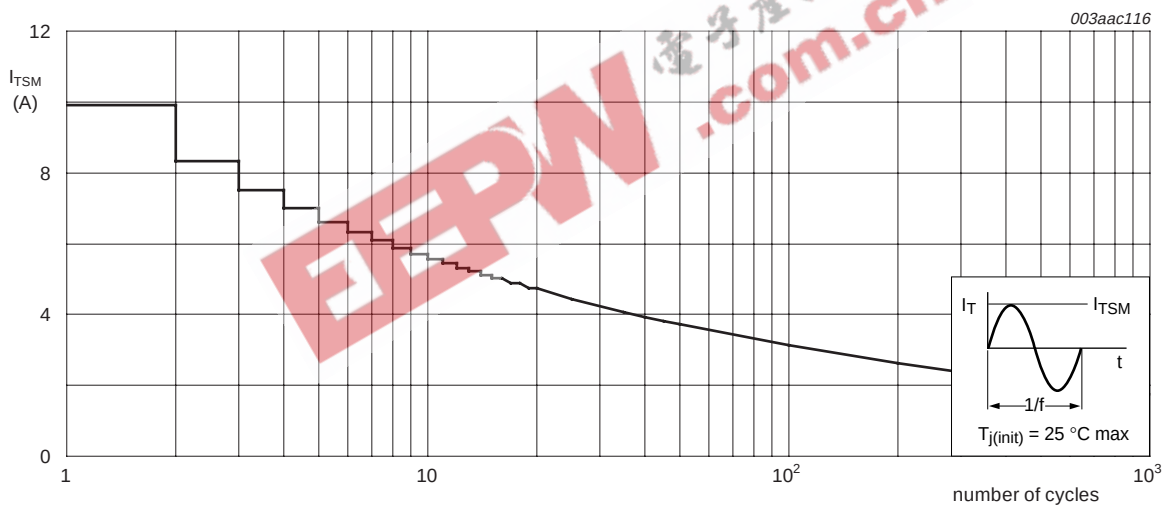
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA2008-600D; BTA2008-600E [1]	-	600	V
		BTA2008-800D; BTA2008-800E	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 70$ °C; see Figure 4 and 5	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		$t = 20$ ms	-	9	A
		$t = 16.7$ ms	-	9.9	A
I^2t	I^2t for fusing	$t_p = 10$ ms	-	0.41	A^2s
dI_T/dt	rate of rise of on-state current	$I_{TM} = 1.5$ A; $I_G = 20$ mA; $dI_G/dt = 0.2$ A/µs	-	100	A/µs
I_{GM}	peak gate current		-	1	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		–40	+150	°C
T_j	junction temperature		-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.



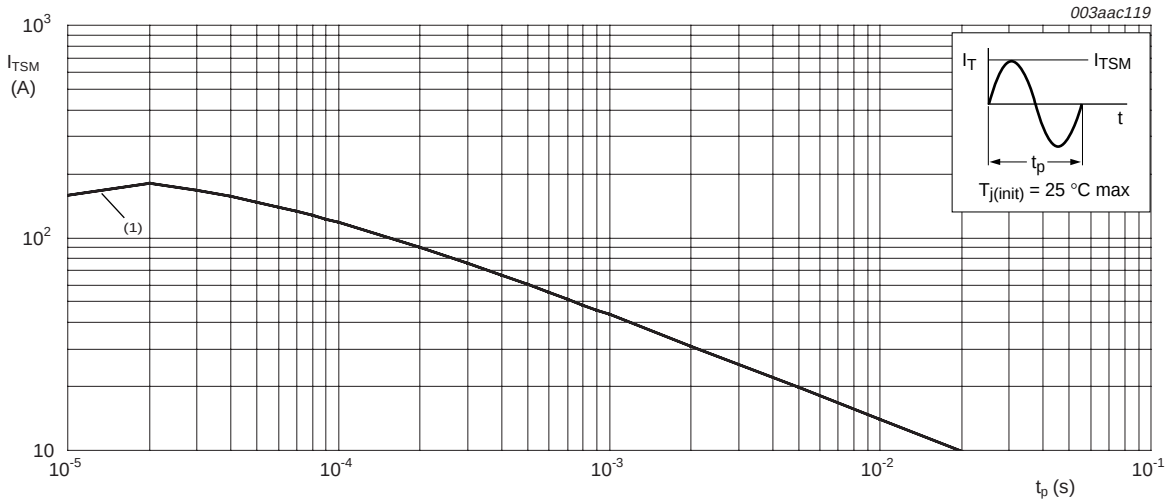
α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

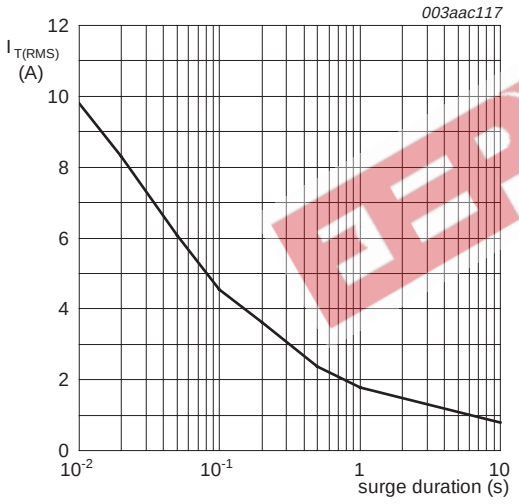
Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



f = 50 Hz

T_{lead} = 70 °C

Fig 4. RMS on-state current as a function of surge duration; maximum values

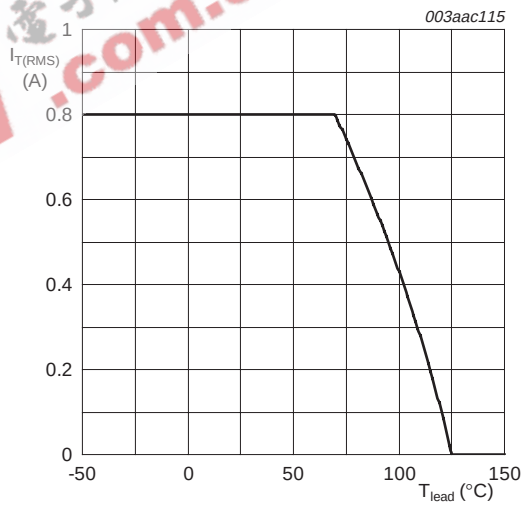


Fig 5. RMS on-state current as a function of lead temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

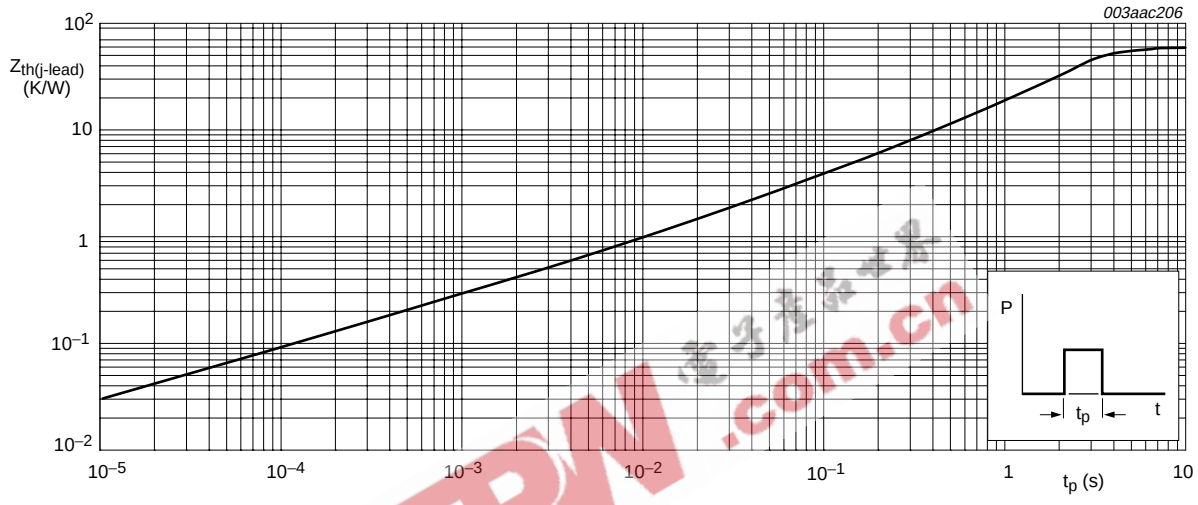


Fig 6. Transient thermal impedance from junction to lead as a function of pulse duration

6. Static characteristics

Table 5. Static characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; see Figure 8							
		T2+ G+	0.25	-	5	0.5	-	10	mA
		T2+ G–	0.25	-	5	0.5	-	10	mA
		T2– G–	0.25	-	5	0.5	-	10	mA
I_L	latching current	V_D = 12 V; I_{GT} = 0.1 A; see Figure 10							
		T2+ G+	-	-	10	-	-	12	mA
		T2+ G–	-	-	20	-	-	20	mA
		T2– G–	-	-	10	-	-	12	mA
I_H	holding current	V_D = 12 V; I_{GT} = 0.1 A; see Figure 11	-	-	10	-	-	12	mA
V_T	on-state voltage	I_T = 0.85 A; see Figure 9	-	1.35	1.6	-	1.35	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; see Figure 7	-	0.9	2	-	0.9	2	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C	0.2	0.3	-	0.2	0.3	-	V
I_D	off-state current	V_D = $V_{DRM(max)}$; T_j = 125 °C	-	0.1	0.5	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125$ °C; exponential waveform; gate open circuit	200	-	-	600	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	$V_{DM} = 400$ V; $T_j = 125$ °C; $I_{T(RMS)} = 0.8$ A; dV/dt = 10 V/µs; gate open circuit	0.5	-	-	1.6	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 1$ A; $V_D = V_{DRM(max)}$; $I_G = 0.1$ A; $dI_G/dt = 5$ A/µs	-	2	-	-	2	-	µs

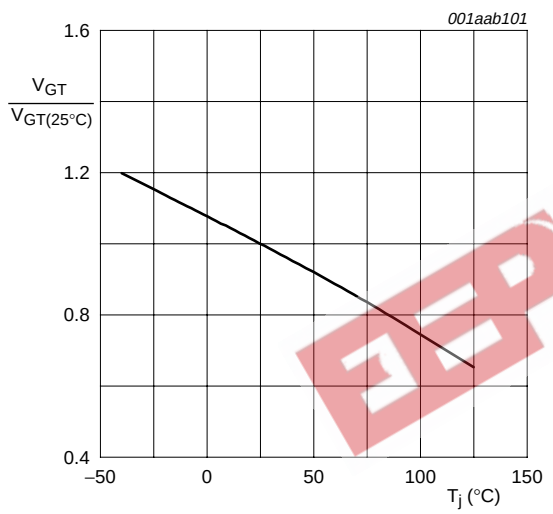
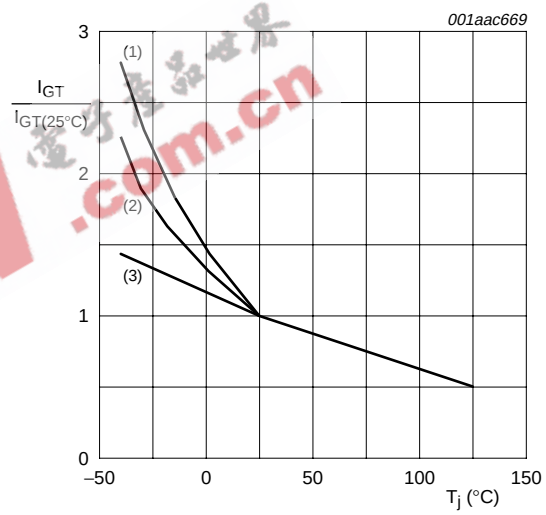
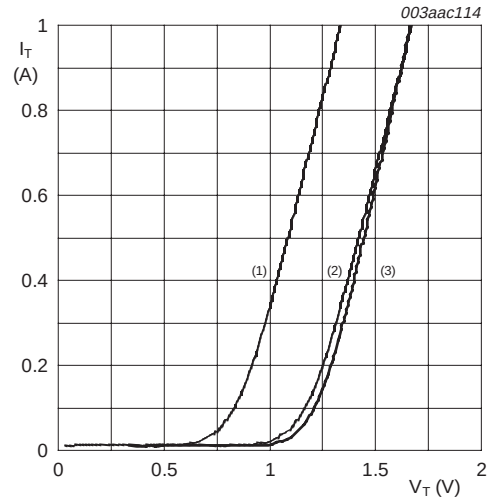


Fig 7. Normalized gate trigger voltage as a function of junction temperature



(1) T2– G–
(2) T2+ G–
(3) T2+ G+

Fig 8. Normalized gate trigger current as a function of junction temperature



V_o = 0.835 V

R_s = 0.5 Ω

(1) T_j = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig 9. On-state current as a function of on-state voltage

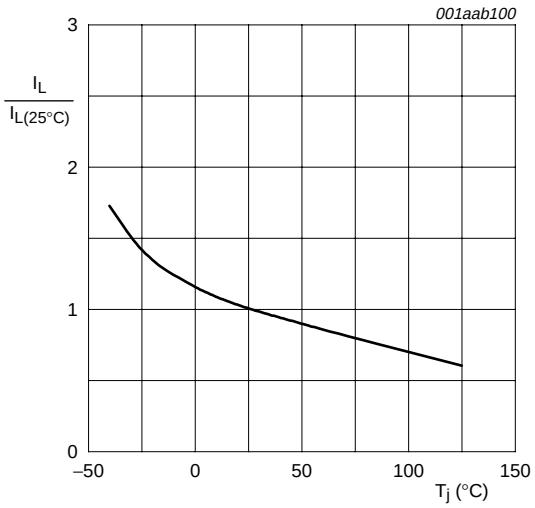


Fig 10. Normalized latching current as a function of junction temperature

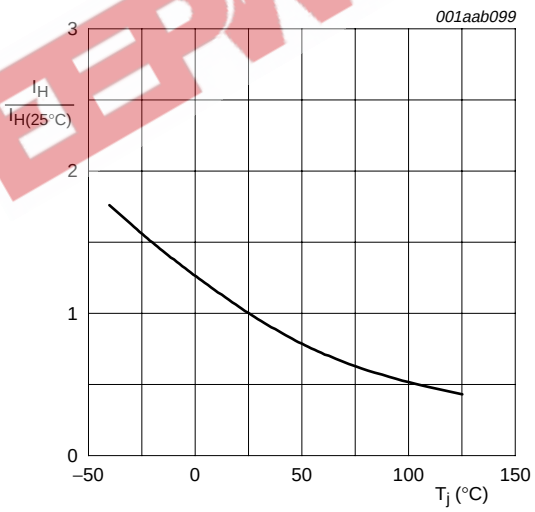
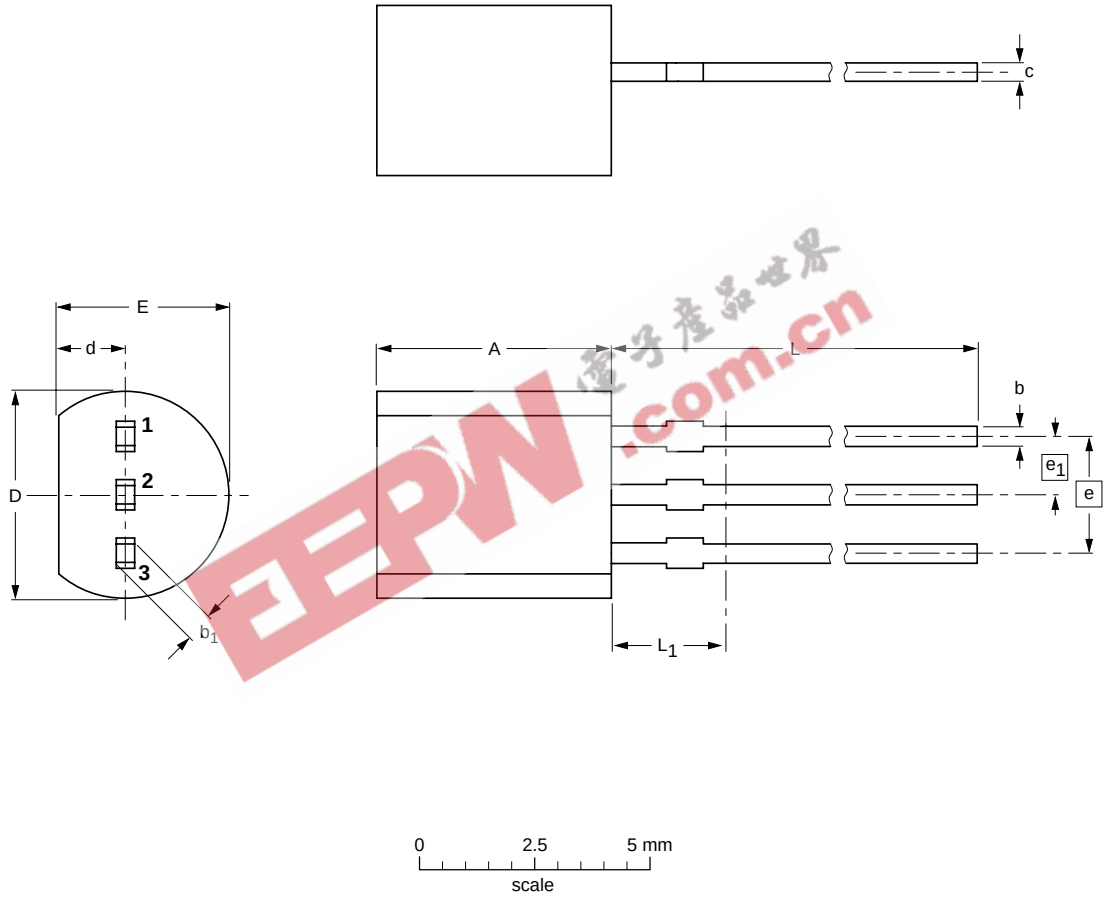


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1(1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~04-06-28~~ 04-11-16

Fig 12. Package outline SOT54 (TO-92)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA2008_SER_D_E_1	20080118	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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12. Contents

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